

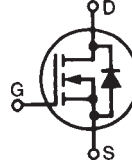
# PolarHV™ HiPerFET

## Power MOSFET

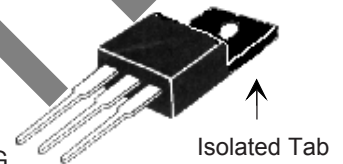
(Electrically Isolated Tab)

**IXFP 8N50PM**
 $V_{DSS} = 500 \text{ V}$   
 $I_{D25} = 4.4 \text{ A}$   
 $R_{DS(on)} \leq 0.8 \text{ } \Omega$   
 $t_{rr} \leq 200 \text{ ns}$ 

N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	4.4	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	14	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	8	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	20	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	300	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 18 \text{ } \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	42	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		4	g

**OVERMOLDED TO-220  
 (IXTP...M) OUTLINE**


G = Gate      D = Drain  
 S = Source

### Features

- † Plastic overmolded tab for electrical isolation
- † International standard package
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
  - easy to drive and to protect
- † Fast Intrinsic Diode

### Advantages

- † Easy to mount
- † Space savings
- † High power density

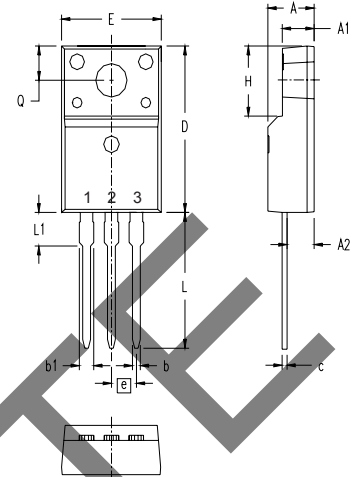
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0 \text{ V}$			5 $\mu\text{A}$ 500 $\mu\text{A}$ $T_J = 125^\circ\text{C}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 4 \text{ A}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			0.8 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 4\text{ A}$	5	8	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1050	pF
$C_{oss}$			120	pF
$C_{rss}$			12	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 8\text{ A}$ $R_G = 18\ \Omega$ (External)		22	ns
$t_r$			28	ns
$t_{d(off)}$			65	ns
$t_f$			23	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 4\text{ A}$		20	nC
$Q_{gs}$			7	nC
$Q_{gd}$			7	nC
$R_{thJS}$				$3.0\ ^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			8 A
$I_{SM}$	Repetitive			14 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 8\text{ A}, V_{GS} = 0\text{ V}, V_R = 100\text{ V}$ $-di/dt = 100\text{ A}/\mu\text{s}$		0.25	200 ns
$Q_{RM}$				$\mu\text{C}$
$I_{RM}$			2	A

### ISOLATED TO-220 (IXTP...M)



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\emptyset P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585  
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